LISTING OF CLAIMS:

The following listing of claims replaces all previous versions and listings of claims in the present application.

1. - 12. (Canceled)

13. (Previously presented) A method of manufacturing a micromechanical structure, comprising the steps of:

forming a stationary element having a stationary element electrode and a movable element having a movable element electrode on a semiconductor substrate, said movable element being formed to be separated from a surface of said semiconductor substrate and movable in a direction parallel to said surface of said semiconductor substrate; and

forming a ~~microstructure~~protuberance on said movable element and opposing surfaces of said stationary element.

14. (Currently amended) A method according to claim 13, wherein the step of forming said ~~microstructure~~protuberance comprises the step of forming a polysilicon thin film on said movable element and ~~at least one of~~ said opposing surfaces of ~~one of~~ said stationary element ~~and said substrate~~ to form a ~~microstructural~~protruding shape on a surface of said polysilicon thin film.

15. (Currently amended) A method according to claim 13, wherein the step of forming said ~~microstructure~~protuberance comprises the step of etching said movable element and ~~at least~~

~~one of~~ said opposing surfaces of ~~one of~~ said stationary element ~~and said substrate~~ to form a ~~microstructural~~protruding shape.

16. (Currently amended) A method of manufacturing a micromechanical structure, said micromechanical structure comprising:

a substrate on which an insulation film is at least partly formed;

a stationary element fixed on said insulating film of said substrate, and having a plurality of stationary element electrodes arranged at a predetermined pitch;

a movable element supported above said substrate by a spring member, said movable element having a plurality of movable element electrodes interdigitized with said stationary element electrodes, said movable element movable in a direction parallel to a surface of said substrate, wherein said stationary element and said movable element each have respective opposing surfaces which are substantially perpendicular to said surface of said substrate; and

a ~~microstructure~~protuberance formed on at least one of said opposing surfaces of said movable element and said stationary element,

said method comprising:

etching a semiconductor layer formed on said substrate to define a structure of said stationary element and said movable element,

wherein said etching includes forming said ~~microstructure~~protuberance on at least one of said opposing surfaces of said movable element and said stationary element.

17. (Previously presented) A method according to claim 16, wherein at least a surface of said stationary element and movable element is formed of polysilicon, and wherein said etching etches said polysilicon.

18. (Currently amended) A method according to claim 16, wherein the forming said ~~microstructure~~protuberance further comprises forming a polysilicon thin film on said movable element and ~~at least one of~~ said opposing surfaces of ~~one of~~ said stationary element ~~and said substrate~~ to form a ~~microstructural~~protruding shape on a surface of said polysilicon thin film.

19. (Currently amended) A method according to claim 16, wherein the forming said ~~microstructure~~protuberance comprises etching said movable element and ~~at least one of~~ said opposing surfaces of ~~one of~~ said stationary element ~~and said substrate~~ to form a ~~microstructural~~protruding shape.